



A Product Line of Diodes Incorporated



**FMMT459** 

# 500V NPN HIGH VOLTAGE TRANSISTOR IN SOT23

#### Feature

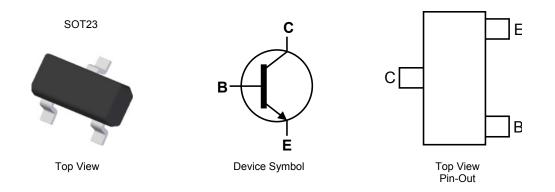
- BV<sub>CEV</sub> > 500V
- BV<sub>ECV</sub> > 6V reverse blocking
- I<sub>C</sub> = 150mA high Continuous Collector Current
- ICM Up to 500mA Peak Pulse Current
- 625mW Power Dissipation
- Low Saturation Voltage <-90mV @ 50mA</li>
- Excellent h<sub>FE</sub> Characteristics Up To 120mA
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (@3)
- Weight 0.008 grams (approximate)

#### **Applications**

- Off-line switching applications
- RCD circuits
- PFC disable switch in PSU
- Emergency lighting
- Piezo actuators
- Telecom protected line switching



#### Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT459TA	AEC-Q101	459	7	8	3,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

Notes:







# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	500	V
Collector-Emitter Voltage	VCEV	500	V
Collector-Emitter Voltage	V <sub>CEO</sub>	450	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Emitter-Collector Voltage	V <sub>ECV</sub>	6	V
Continuous Collector Current	Ic	150	mA
Peak Pulse Current	Ісм	500	mA
Base Current	IB	200	mA

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	625	mW
Power Dissipation (Note 6)	PD	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R <sub>0JL</sub>	194	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	٥°

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

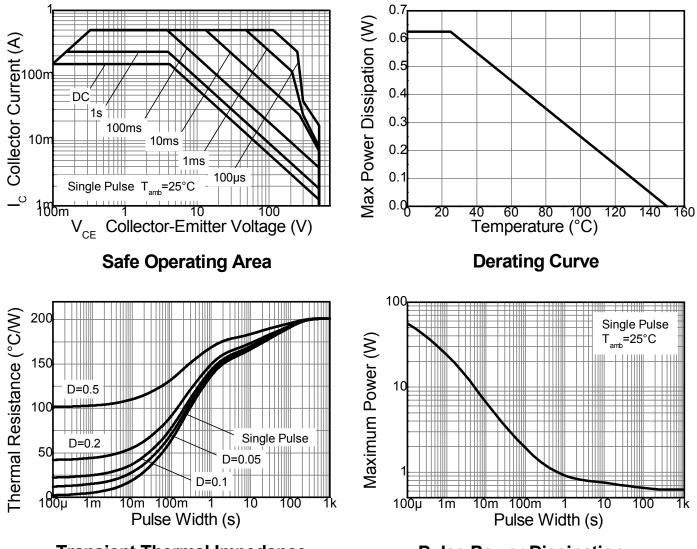
6. Same as note 5, except the device is measured at t  $\leq$  5 sec.

Thermal resistance from junction to solder-point (at the end of the collector lead).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.





# Thermal Characteristics and Derating Information



**Transient Thermal Impedance** 

**Pulse Power Dissipation** 





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

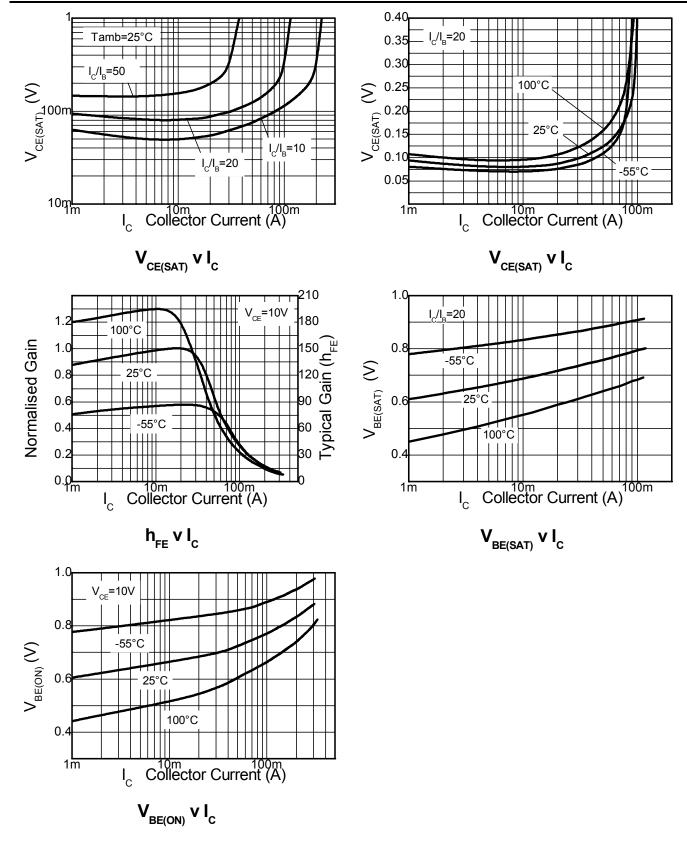
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	500	700	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CEV</sub>	500	700	—	V	I <sub>C</sub> = 10μA; 0.3V > V <sub>BE</sub> > -1V
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	450	500	—	V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	_	V	I <sub>E</sub> = 100μA
Emitter-Base Breakdown Voltage (Reverse Blocking)	BV <sub>ECV</sub>	6	8.1	—	V	I <sub>C</sub> = 1μA; 0.3V > V <sub>BC</sub> > -6V
Collector Cutoff Current	I <sub>CBO</sub>	—	<10	100	nA	V <sub>CB</sub> = 450V
Emitter Cutoff Current	I <sub>EBO</sub>	—	<10	100	nA	V <sub>EB</sub> = 5.6V
Collector Emitter Cutoff Current	I <sub>CES</sub>	—	<10	100	nA	V <sub>CE</sub> = 450V
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	50	120	—	—	I <sub>C</sub> = 30mA, V <sub>CE</sub> = 10V
Static Folward Current Transfer Ratio (Note 9)		—	70	_		I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V
Collector-Emitter Saturation Voltage (Note 9)	Vorum	—	60	75	mV	I <sub>C</sub> = 20mA, I <sub>B</sub> = 2mA
	V <sub>CE(sat)</sub>	—	70	90	mV	I <sub>C</sub> = 50mA, I <sub>B</sub> = 6mA
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	—	0.71	0.9	V	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 10V
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	—	0.76	0.9	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5mA
Output Capacitance	C <sub>obo</sub>	—	—	5	pF	V <sub>CB</sub> = 20V, f = 1MHz
Transition Frequency	f <sub>T</sub>	50	-		MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 20MHz
Turn-On Time	t <sub>on</sub>	—	113		ns	$V_{\rm C} = 100V, I_{\rm C} = 50mA$
Turn-Off Time	t <sub>off</sub>	_	3450	_	ns	$I_{B1} = 5mA$ , $I_{B2} = -10mA$

9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%. Notes:





# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

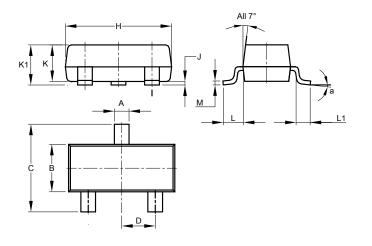






# **Package Outline Dimensions**

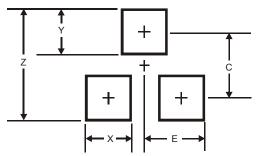
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
Κ	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	8°				
All	Dimens	ions in	mm		

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking. Note:





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